



IRF840

N-CHANNEL 500V - 0.75Ω - 8A TO-220

PowerMesh™II MOSFET

| TYPE | V _{DSS} | R _{DS(on)} | I _D |
|--------|------------------|---------------------|----------------|
| IRF840 | 500 V | < 0.85 Ω | 8 A |

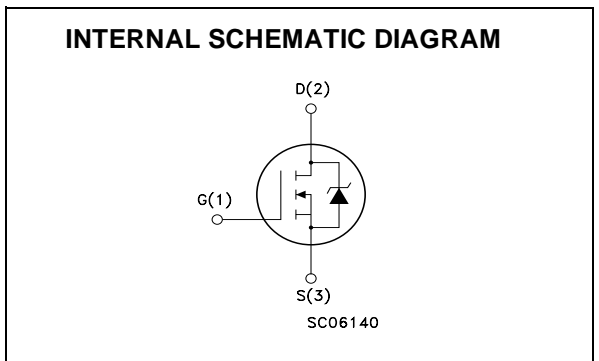
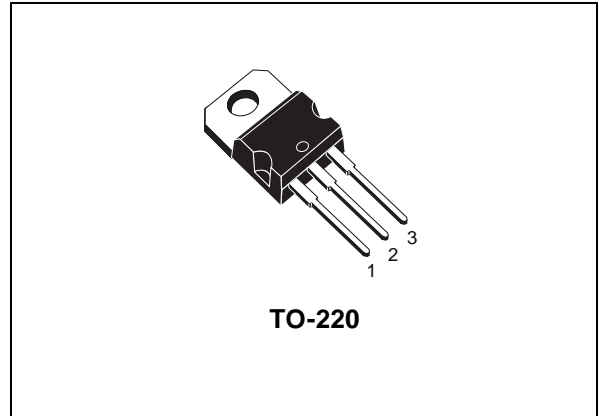
- TYPICAL R_{DS(on)} = 0.75 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- NEW HIGH VOLTAGE BENCHMARK
- GATE CHARGE MINIMIZED

DESCRIPTION

The PowerMESH™II is the evolution of the first generation of MESH OVERLAY™. The layout refinements introduced greatly improve the Ron*area figure of merit while keeping the device at the leading edge for what concerns switching speed, gate charge and ruggedness.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVES



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|---------------------|--|------------|------|
| V _{DS} | Drain-source Voltage (V _{GS} = 0) | 500 | V |
| V _{DGR} | Drain-gate Voltage (R _{GS} = 20 kΩ) | 500 | V |
| V _{GS} | Gate- source Voltage | ± 20 | V |
| I _D | Drain Current (continuous) at T _C = 25°C | 8 | A |
| I _D | Drain Current (continuous) at T _C = 100°C | 5.1 | A |
| I _{DM} (•) | Drain Current (pulsed) | 32 | A |
| P _{TOT} | Total Dissipation at T _C = 25°C | 125 | W |
| | Derating Factor | 1.0 | W/°C |
| dv/dt (1) | Peak Diode Recovery voltage slope | 3.5 | V/ns |
| T _{stg} | Storage Temperature | -65 to 150 | °C |
| T _j | Max. Operating Junction Temperature | 150 | °C |

(•)Pulse width limited by safe operating area

(1)I_{SD} ≤ 8A, di/dt ≤ 50A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}.

THERMAL DATA

| | | | |
|----------------|--|------|------|
| Rthj-case | Thermal Resistance Junction-case Max | 1 | °C/W |
| Rthj-amb | Thermal Resistance Junction-ambient Max | 62.5 | °C/W |
| T _l | Maximum Lead Temperature For Soldering Purpose | 300 | °C |

AVALANCHE CHARACTERISTICS

| Symbol | Parameter | Max Value | Unit |
|-----------------|--|-----------|------|
| I _{AR} | Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max) | 8 | A |
| E _{AS} | Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V) | 520 | mJ |

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|----------------------|---|---|------|------|---------|----------|
| V _{(BR)DSS} | Drain-source Breakdown Voltage | I _D = 250 μA, V _{GS} = 0 | 500 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current (V _{GS} = 0) | V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C | | | 1 50 | μA μA |
| I _{GSS} | Gate-body Leakage Current (V _{DS} = 0) | V _{GS} = ± 20V | | | ±100 | nA |

ON (1)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------|-----------------------------------|--|------|------|------|------|
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} , I _D = 250μA | 2 | 3 | 4 | V |
| R _{DS(on)} | Static Drain-source On Resistance | V _{GS} = 10V, I _D = 3.5 A | | 0.75 | 0.85 | Ω |

DYNAMIC

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------|------------------------------|--|------|------|------|------|
| g _{fs} (1) | Forward Transconductance | V _{DS} > I _{D(on)} × R _{DS(on)max} , I _D = 3.5A | | 6.4 | | S |
| C _{iss} | Input Capacitance | V _{DS} = 25V, f = 1 MHz, V _{GS} = 0 | | 832 | | pF |
| C _{oss} | Output Capacitance | | | 131 | | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 17 | | pF |

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|----------------------|---------------------------------|--|------|----------|------|----------|
| $t_{d(on)}$ t_r | Turn-on Delay Time Rise Time | $V_{DD} = 250\text{ V}$, $I_D = 3.5\text{ A}$ $R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3) | | 10 21 | | ns ns |
| Q_g | Total Gate Charge | $V_{DD} = 400\text{ V}$, $I_D = 7\text{ A}$, $V_{GS} = 10\text{ V}$ | | 29.6 | 39 | nC |
| Q_{gs} | Gate-Source Charge | | | 4.9 | | nC |
| Q_{gd} | Gate-Drain Charge | | | 13.9 | | nC |

SWITCHING OFF

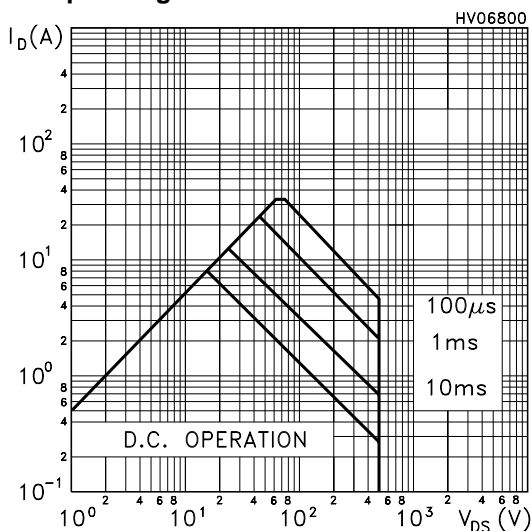
| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|----------------|-----------------------|--|------|------|------|------|
| $t_r(V_{off})$ | Off-voltage Rise Time | $V_{DD} = 400\text{ V}$, $I_D = 7\text{ A}$, $R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 5) | | 9 | | ns |
| t_f | Fall Time | | | 9 | | ns |
| t_c | Cross-over Time | | | 19 | | ns |

SOURCE DRAIN DIODE

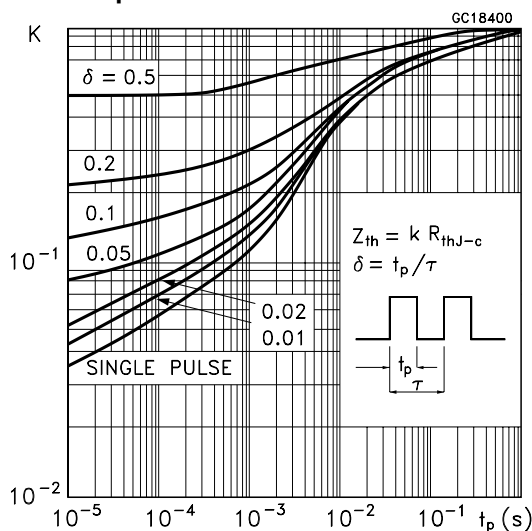
| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------------|-------------------------------|---|------|------|------|---------------|
| I_{SD} | Source-drain Current | | | | 8 | A |
| $I_{SDM(2)}$ | Source-drain Current (pulsed) | | | | 32 | A |
| $V_{SD(1)}$ | Forward On Voltage | $I_{SD} = 8\text{ A}$, $V_{GS} = 0$ | | | 1.6 | V |
| t_{rr} | Reverse Recovery Time | $I_{SD} = 7\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$, $T_J = 150^\circ\text{C}$ (see test circuit, Figure 5) | | 384 | | ns |
| Q_{rr} | Reverse Recovery Charge | | | 2.2 | | μC |
| I_{RRM} | Reverse Recovery Current | | | 11.8 | | A |

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

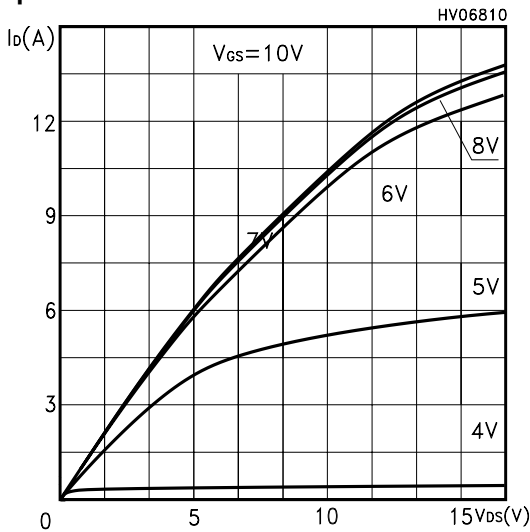
Safe Operating Area



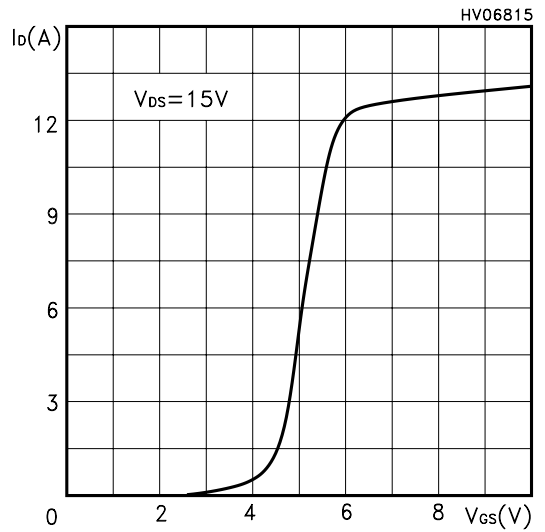
Thermal Impedance



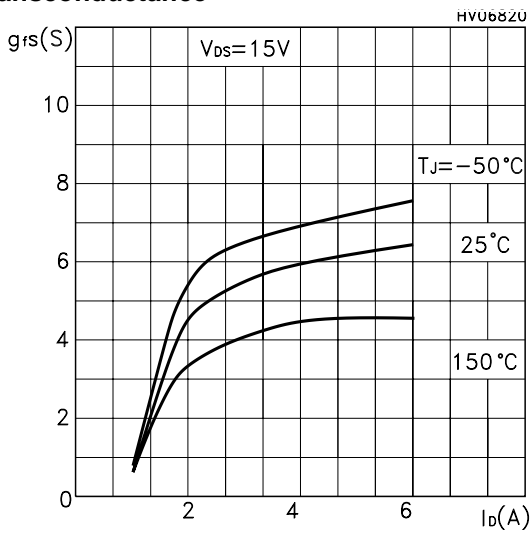
Output Characteristics



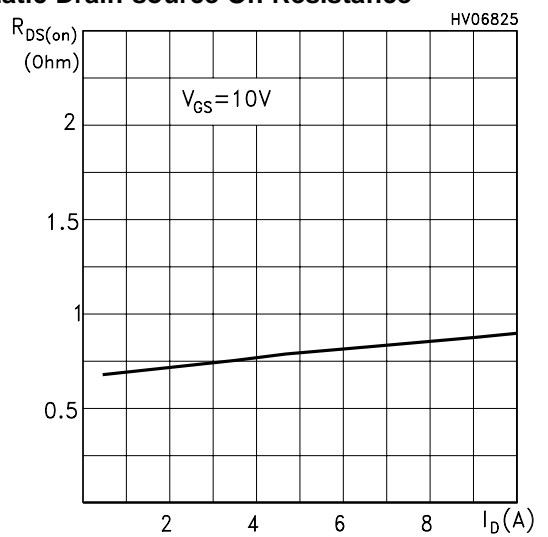
Transfer Characteristics



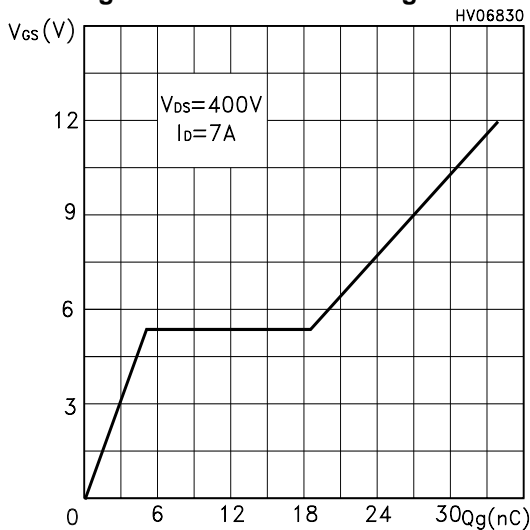
Transconductance



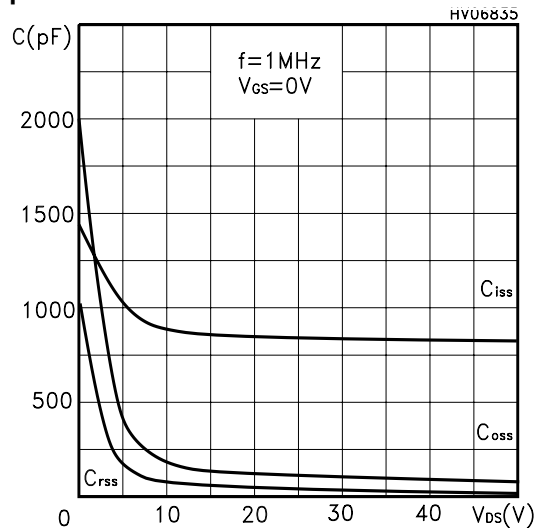
Static Drain-source On Resistance



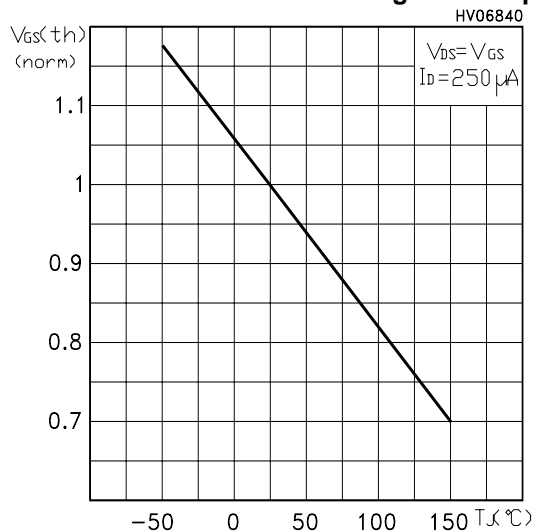
Gate Charge vs Gate-source Voltage



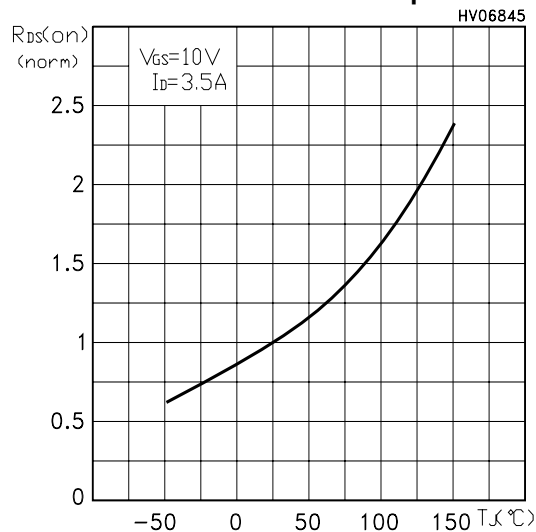
Capacitance Variations



Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

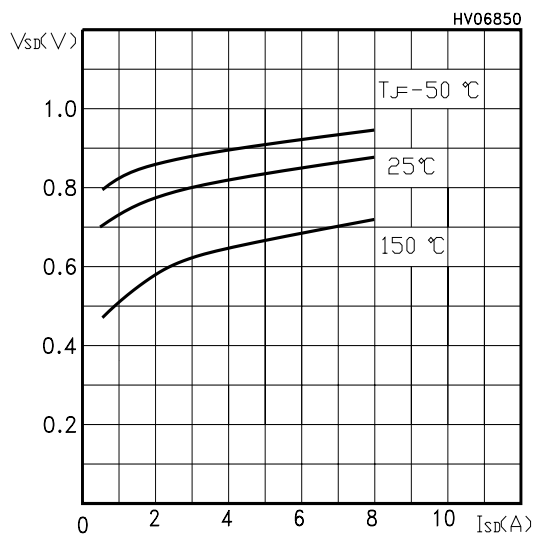


Fig. 1: Unclamped Inductive Load Test Circuit

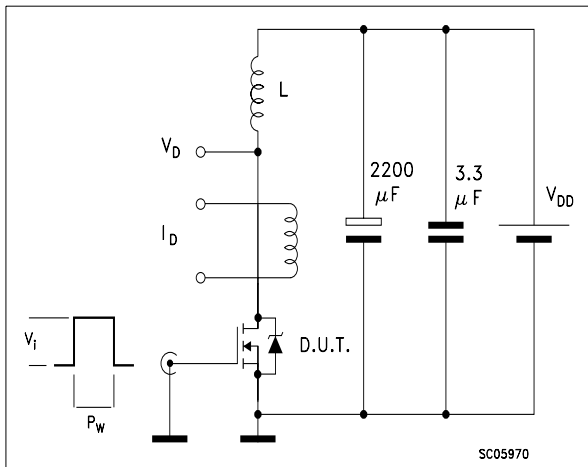


Fig. 2: Unclamped Inductive Waveform

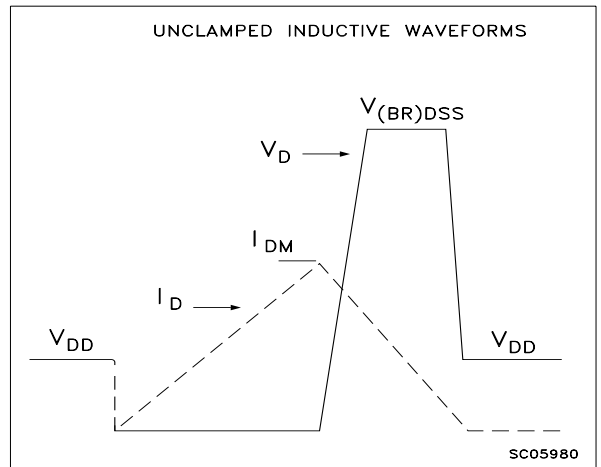


Fig. 3: Switching Times Test Circuit For Resistive Load

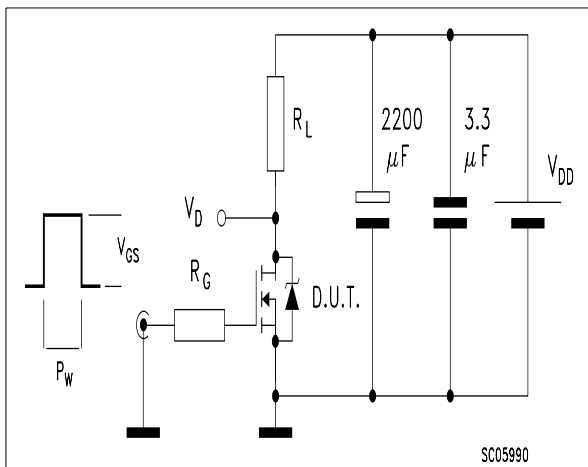


Fig. 4: Gate Charge test Circuit

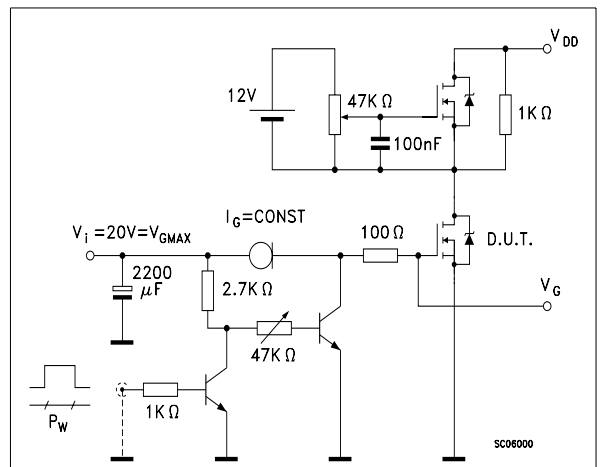
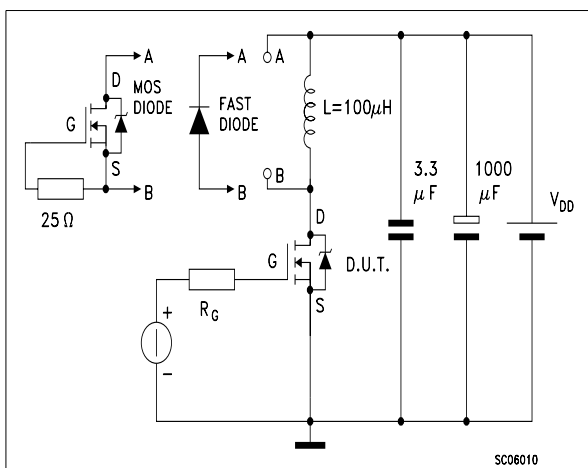
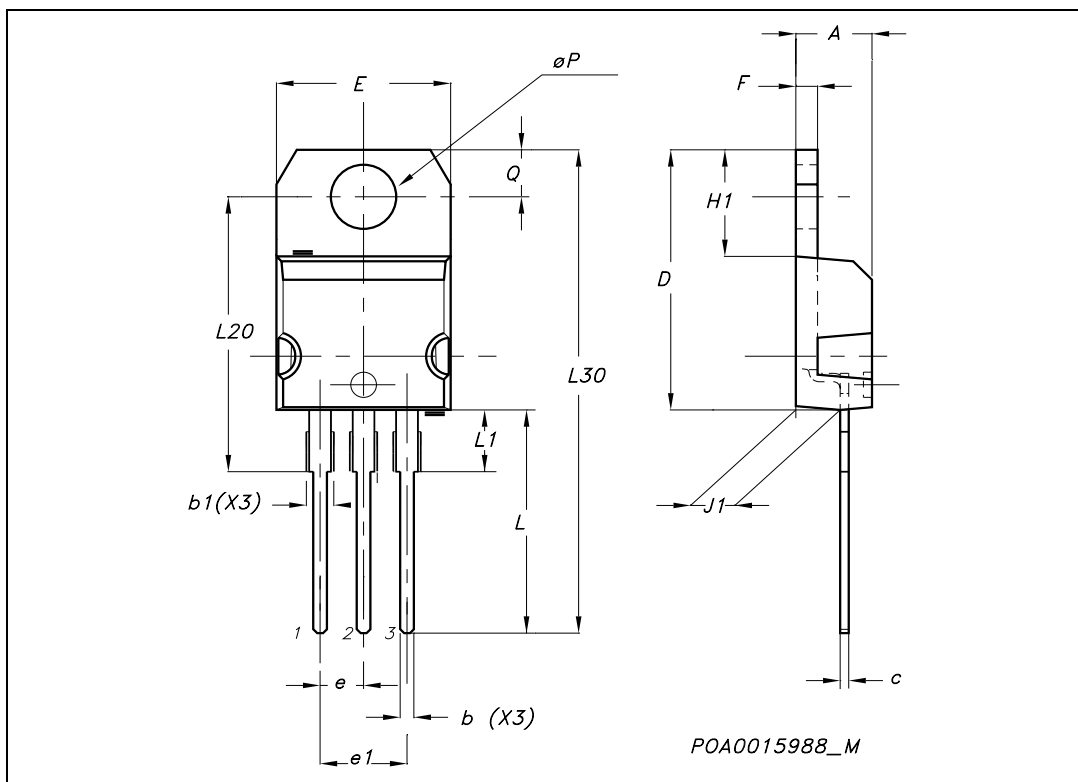


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-220 MECHANICAL DATA

| DIM. | mm. | | | inch | | |
|----------|-------|-------|-------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 4.40 | | 4.60 | 0.173 | | 0.181 |
| b | 0.61 | | 0.88 | 0.024 | | 0.034 |
| b1 | 1.15 | | 1.70 | 0.045 | | 0.066 |
| c | 0.49 | | 0.70 | 0.019 | | 0.027 |
| D | 15.25 | | 15.75 | 0.60 | | 0.620 |
| E | 10 | | 10.40 | 0.393 | | 0.409 |
| e | 2.40 | | 2.70 | 0.094 | | 0.106 |
| e1 | 4.95 | | 5.15 | 0.194 | | 0.202 |
| F | 1.23 | | 1.32 | 0.048 | | 0.052 |
| H1 | 6.20 | | 6.60 | 0.244 | | 0.256 |
| J1 | 2.40 | | 2.72 | 0.094 | | 0.107 |
| L | 13 | | 14 | 0.511 | | 0.551 |
| L1 | 3.50 | | 3.93 | 0.137 | | 0.154 |
| L20 | | 16.40 | | | 0.645 | |
| L30 | | 28.90 | | | 1.137 | |
| ϕP | 3.75 | | 3.85 | 0.147 | | 0.151 |
| Q | 2.65 | | 2.95 | 0.104 | | 0.116 |



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